
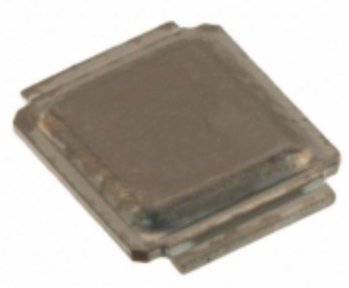











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|---|---|
|  | <p>BSB012NE2LX</p> |
| | <p>Hersteller-Teilenummer: BSB012NE2LX</p> |
|  | <p>Hersteller / Marke: International Rectifier (Infineon Technologies)</p> |
| | <p>Teil der Beschreibung: MOSFET N-CH 25V 170A WDSO-2</p> |
| | <p>Datenblätter:  BSB012NE2LX.pdf</p> |
| | <p>RoHs Status: Bleifrei / RoHS-konform</p> |
| | <p>Lagerzustand: New original, 1000 pcs Stock Available.</p> |
| | <p>Liefern von: Hong Kong</p> |
| <p>Image may be representation. See specs for product details.</p> | <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p> |

Spezifikationen

| | |
|---|--|
| Teilenummer | BSB012NE2LX |
| Hersteller | International Rectifier (Infineon Technologies) |
| Beschreibung | MOSFET N-CH 25V 170A WDSO-2 |
| Kategorie | Diskrete Halbleiterprodukte > Transistoren-FETs, |
| Teilstatus | 1000 pcs Stock |
| Serie | OptiMOS™ |
| Technologie | MOSFET (Metal Oxide) |
| Betriebstemperatur | -40°C ~ 150°C (TJ) |
| Befestigungsart | Surface Mount |
| Verpackung / Gehäuse | 3-WDSO-2 |
| Supplier Device-Gehäuse | MG-WDSO-2, CanPAK M™ |
| Verlustleistung (max) | 2.8W (Ta), 57W (Tc) |
| Typ FET | N-Channel |
| FET-Merkmal | - |
| Drain-Source-Spannung (Vdss) | 25V |
| Strom - Ununterbrochener Abfluss (Id) bei 25 °C | 37A (Ta), 170A (Tc) |
| Rds On (Max) @ Id, Vgs | 1.2 mOhm @ 30A, 10V |
| VGS (th) (Max) @ Id | 2V @ 250µA |
| Gate Charge (Qg) (Max) @ Vgs | 67nC @ 10V |
| Eingabekapazität (Ciss) (Max) @ Vds | 4900pF @ 12V |
| Verpackung | Tape & Reel (TR) |

BSB012NE2LX ist neu im Original, Suche BSB012NE2LX Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie BSB012NE2LX International Rectifier (Infineon Technologies) mit Garantie und Vertrauen. Anfrage BSB012NE2LX: Info@Y-IC.com

Sie können auch interessiert sein:

| | | | |
|--|---|--|--|
|  <p>BSB014N04LX3G International Rectifier (Infineon Technologies) BSB014N04LX3G INFINEON</p> |  <p>BSB008NE2LX INFINEON INFINEON WDSO-2</p> |  <p>BSB013NE2LXI International Rectifier (Infineon Technologies) BSB013NE2LXI Infineon Technologies</p> |  <p>BSB008NE2LXXUMA1 International Rectifier (Infineon Technologies) MOSFET N-CH 25V 46A 2WDSO-2</p> |
|  <p>BSB012NE2LX5G INFINEON BSB012NE2LX5G INFINEON</p> |  <p>BSB012NE2LXIXUMA1 International Rectifier (Infineon Technologies) MOSFET N-CH 25V 170A WDSO-2</p> |  <p>BSB014N04LX3 G International Rectifier (Infineon Technologies) MOSFET N-CH 40V 180A 2WDSO-2</p> |  <p>BSB012N03LX3 G International Rectifier (Infineon Technologies) MOSFET N-CH 30V 180A 2WDSO-2</p> |

heiße Teile

Mehr

- | | | | | |
|------------------|--------------------|-------------------|----------------------|----------------------|
| ⊗ 06035C222K4T2A | ↔ 12065C333KAT2M | ⇒ 6MBI75VW-060-50 | D A2405D-1W | ⇒ AD71001JRRL |
| ⊣ AIC1660CS | ⊗ AP18N20GP-HF | D BAW567DW-7-F | ⇒ BD6046GUL-E2 | ⇒ BSB012NE2LX5G |
| ⊗ BSB012NE2LXI | ⊣ BSB013NE2LXI | ⊗ BSB014N04LX3G | ↔ BSB015N04NX3G | ⇒ BSB017N03LX3G |
| D BSB018NE2LXG | ⊗ BSB019N03LXG | ⊣ BSB024N03LXG | ⊗ BSB028N06NN3G | ⇒ BSB053N03LPG |
| ⇒ BSB053N03LTG | ↔ BSB056N10NN3G | ⊗ BSB104N08NP3G | ⊣ BSB105N04NX3G | ⇒ BSB165N15NZ3G |
| ↔ BU7680G-TR | ⇒ DRC3114EOL | D DS2101SY14 | ⊗ EP1C4F324I7 | ⊣ FAN1851AMX |
| ⊗ FDZ3N513ZT | D FSUSB11MTCX | ⇒ LD035C561JAB2A | ↔ LNBH24TPPR | ⇒ MC9S12B128MFUE |
| ⊣ MG200Q1ZS40 | ⊗ MLK1005S15NJT000 | ↔ MMSZ4689 | ⇒ NC7SP58P6X | ⇒ S-93C86BD4H-T8T2UD |
| ⊗ SI7440DP-T1-E3 | ⊣ SM6A27HE3/2D | ⊗ SMF8V0A-HE3-08 | D SN74LVC1G126DCKR-P | ⇒ SQ9407EY-T1-GE3 |
| ↔ TPCS8303 | ⊗ TPS756151KTT | ⊣ TYPE8P2S-A | ⊗ VI-2W2-EW | ⇒ ZUW62415 |

Contact us: Info@Y-IC.com

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

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